

4K x 8/9 Dual-Port Static RAM with Sem, Int, Busy

Features

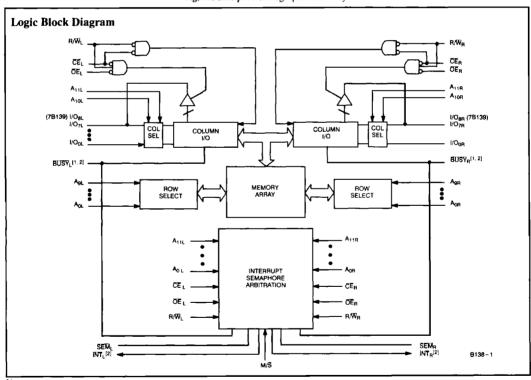
- 0.8-micron BiCMOS for high performance
- High-speed access
 - 15 ns (com'l)
 - 25 ns (mil)
- Automatic power-down
- Fully asynchronous operation
- Master /Slave select pin allows bus width expansion to 16/18 bits or more
- Busy arbitration scheme provided
- Semaphores included to permit software handshaking between ports
- INT flag for port-to-port communication
- Available in 68-pin LCC/PLCC/PGA
- TTL compatible

Functional Description

The CY7B138 and CY7B139 are highspeed BiCMOS 4K x 8 and 4K x 9 dual-port static RAMs. Various arbitration schemes are included on the CY7B138/9 to handle situations when multiple processors access the same piece of data. Two ports are provided permitting independent, asynchronous access for reads and writes to any location in memory. The CY7B138/9 can be utilized as a standalone 32-Kbit dual-port static RAM or multiple devices can be combined in order to function as a 16/18-bit or wider master/ slave dual-port static RAM. An M/S pin is provided for implementing 16/18-bit or wider memory applications without the need for separate master and slave devices or additional discrete logic. Application areas include interprocessor/multiprocessor designs, communications status buffering, and dual-port video/graphics memory.

Each port has independent control pins: chip enable (CE), read or write enable (R/W), and output enable (\overline{OE}) . Two flags are provided on each port (BUSY and INT). BUSY signals that the port is trying to access the same location currently being accessed by the other port. The interrupt flag (INT) permits communication between ports or systems by means of a mail box. The semaphores are used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphore logic is comprised of eight shared latches. Only one side can control the latch (semaphore) at any time. Control of a semaphore indicates that a shared resource is in use. An automatic power-down feature is controlled independently on each port by a chip enable (CE) pin or SEM pin.

The CY7B138 and CY7B139 are available in 68-pin LCCs, and PLCCs.

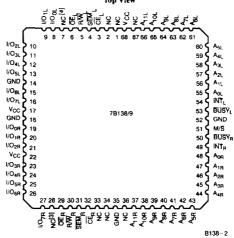


Notes:
1. BUSY is an output in master mode and an input in slave mode.

2. Master: push-pull output and requires no pull-up resistor.

Pin Configuration

68-Pin LCC/PLCC Top View



Pin Definitions

Left Port	Right Port	Description
I/O _{0L-7L(8L)}	I/O _{(IR-7R(8R)}	Data Bus Input/Output
A _{0L-11L}	A _{0R-11R}	Address Lines
<u>CE</u> L	CER	Chip Enable
ŌĒL	ŌĒ _R	Output Enable
R/W _L	R/W _R	Read/Write Enable
SEML	SEM _R	Semaphore Enable. When asserted LOW, allows access to eight semaphores. The three least significant bits of the address lines will determine which semaphore to write or read. The 1/O ₀ pin is used when writing to a semaphore. Semaphores are requested by writing a 0 into the respective location.
ĪNT _L	INT _R	Interrupt Flag. INT _L is set when right port writes location FFE and is cleared when left port reads location FFE. INT _R is set when left port writes location FFF and is cleared when right port reads location FFF.
BUSYL	BUSYR	Busy Flag
M/S		Master or Slave Select
V _{CC}		Power
GND		Ground

Selection Guide

		7B138-15 7B139-15	7B138-25 7B139-25	7B138-35 7B139-35	7B138-55 7B139-55
Maximum Access Time (ns)		15	25	35	55
Maximum Operating	Commercial	260	220	210	210
Current (mA)	Military/Industrial		280	250	250
Maximum Standby	Commercial	110	95	90	90
Current for I _{SB1} (mA)	Military/Industrial		100	95	95



Maximum Ratings

Static Discharge Voltage	>2001V
Latch-Up Current	>200 mA

Operating Range

Range	Ambient Temperature	v _{cc}
Commercial	0°C to +70°C	5V ± 10%
Industrial	-40°C to +85°C	5V ± 10%
Military ^[4]	-55°C to +125°C	5V ± 10%

DC Input Voltage^[3] -0.5V to +7.0V

				8-15 9-15		8-25 9-25		
Parameter	Description	Test Conditions		Min.	Max.	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -4.0 \text{ m}$	A	2.4		2.4		V
V _{OL}	Output LOW Voltage	$V_{CC} = Min., I_{Ol.} = 4.0 \text{ mA}$			0.4		0.4	V
V_{1H}	Input HIGH Voltage			2.2		2.2		V
V _{IL}	Input LOW Voltage				0.8		0.8	V
I _{IX}	Input Leakage Current	$GND \le V_I \le V_{CC}$		-10	+10	-10	+10	μA
I _{OZ}	Output Leakage Current	Output Disabled, GND ≤ V _C	$\leq V_{CC}$	-10	+10	-10	+10	μA
I _{CC}	Operating Current	$V_{CC} = Max.$	Com'l		260		220	mA
		I _{OUT} = 0 mA, Outputs Disabled	Mil/Ind				280	1
I _{SBI}	Standby Current	\overline{CE}_L and $\overline{CE}_R \ge V_{IH}$, $f = f_{MAX}^{[6]}$	Com'l		110		95	mA
	(Both Ports TTL Levels)	$f = f_{MAX}^{[6]}$	Mil/Ind				100	1
I _{SB2}	Standby Current	\overline{CE}_L and $\overline{CE}_R \ge V_{IH}$, $f = f_{MAX}^{[6]}$	Com'l		165		145	mA
	(One Port TTL Level)	$f = f_{MAX}^{[n]}$	Mil/Ind				180	1
I _{SB3}	Standby Current (Both Ports CMOS Levels)	Both Ports \overline{CE} and $\overline{CE}_R \ge V_{CC} - 0.2V$,	Com'l		15		15	mA
		$V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, $f = 0^{ 6 }$	Mil/Ind				30]
I _{SB4}	Standby Current (One Port CMOS Level)	One Port $\overline{CE}_{R} \ge V_{CC} = 0.2V$,	Com'l		160		140	mA
		$V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, Active Port Outputs, $f = f_{MAX}^{[6]}$	Mil/Ind				160	1

Notes:

- 3. Pulse width < 20 ns.
- 4. TA is the "instant on" case temperature.
- See the last page of this specification for Group A subgroup testing information.
- f_{MAX} = 1/t_{RC} = All inputs cycling at f = 1/t_{RC} (except output enable).
 f = 0 means no address or control lines change. This applies only to inputs at CMOS level standby I_{SB3}.



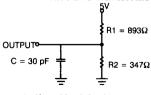
Electrical Characteristics Over the Operating Range^[5] (continued)

					8-35 9-35		8-55 9-55	
Parameter	Description	Test Conditions	Min.	Max.	Min.	Max.	Unit	
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -4.0 \text{ m}$	A	2.4		2.4		V
V _{OL}	Output LOW Voltage	$V_{CC} = Min.$, $I_{OL} = 4.0 \text{ mA}$			0.4		0.4	V
V _{IH}	Input HIGH Voltage			2.2		2.2		V
V _{IL}	Input LOW Voltage				0.8		0.8	V
I _{IX}	Input Leakage Current	$GND \le V_1 \le V_{CC}$		-10	+10	-10	+10	μА
loz	Output Leakage Current	Output Disabled, GND ≤ V ₍	$0 \le V_{CC}$	-10	+10	-10	+10	μA
l _{CC}	Operating Current	$V_{CC} = Max.,$ $I_{OUT} = 0 \text{ mA},$	Com'l		210		210	mA
		Outputs Disabled	Mil/Ind		250		250	
I _{SB1}	Standby Current	\overline{CE}_L and $\overline{CE}_R \ge V_{IH}$, $f = f_{MAX}^{[6]}$	Com'l		90		90	mA
	(Both Ports TTL Levels)	$f = f_{MAX}^{[h]}$	Mil/Ind		95	1	95	1
l_{SB2}	Standby Current	\overline{CE}_L and $\overline{CE}_R \ge V_{IH}$, $f = f_{MAX}^{[6]}$	Com'l		135		135	mA
	(One Port TTL Level)	$f = f_{MAX}^{\{b\}}$	Mil/Ind		160		160	1
I _{SB3}	Standby Carrent (Both Ports CMOS Levels)	Both Ports \overline{CE} and $\overline{CE}_R \ge V_{CC} - 0.2V$,	Com'l		15		15	mA
		$V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, $f = 0^{[6]}$	Mil/Ind		30		30	
I _{SB4}	Standby Current (One Port CMOS Level)	One Port \overline{CE}_{L} or $\overline{CE}_{R} \ge V_{CC} - 0.2V$,	Com'l		130		130	mA
		CE _L or CE _R \geq V _{CC} $-$ 0.2V, V _{IN} \geq V _{CC} $-$ 0.2V or V _{IN} \leq 0.2V, Active Port Outputs, $f = f_{MAX}^{[6]}$	Mil/Ind		140		140	

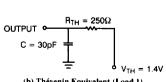
Capacitance^[7]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	10	pF
Cour	Output Capacitance	$V_{CC} = 5.0V$	15	nF

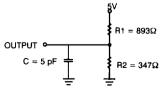
AC Test Loads and Waveforms



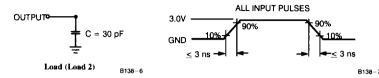
(a) Normal Load (Load 1) B138-3



(b) Thévenin Equivalent (Load 1)



(c) Three-State Delay (Load 3) B138-5



Note:
7. Tested initially and after any design or process changes that may affect these parameters.



Switching Characteristics Over the Operating Range [5, 8]

			38-15 39-15		38-25 39-25		38-35 39-35		38-55 39-55	
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCL	Æ									
t _{RC}	Read Cycle Time	15		25		35		55		ns
t _{AA}	Address to Data Valid		15		25		35		55	ns
¹ OHA	Output Hold From Address Change	3		3		3		3		ns
t _{ACE}	CE LOW to Data Valid		15		25		35		55	ns
t _{DOE}	OE LOW to Data Valid		10		15		20		25	ns
t _{LZOE} [9, 10]	OE Low to Low Z	3		3		3	<u> </u>	3	<u> </u>	ns
t _{HZOE} [9, 10]	OE HIGH to High Z		10		15		20		25	ns
t _{LZCE} [9, 10]	CE LOW to Low Z	3		3		3		3	1	ns
t _{HZCE} [9, 10]	CE HIGH to High Z		10		15		20		25	ns
tpU	CE LOW to Power-Up	0		0		0		0		ns
t _{PD}	CE HIGH to Power-Down		15		25		35		55	ns
WRITE CYC	LE				·					
twc	Write Cycle Time	15		25		35		55		ns
tSCE	CE LOW to Write End	12		20		30		40		ns
t _{AW}	Address Set-Up to Write End	12	_	20	1	30		40		ns
t _{HA}	Address Hold From Write End	2		2		2		2		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		0		ns
tpwE	Write Pulse Width	12		20		25		30		ns
t _{SD}	Data Set-Up to Write End	10	<u> </u>	15		15		20		ns
tHD	Data Hold From Write End	0		0		0		0		ns
t _{HZWE} [10]	R/W LOW to High Z		10		15		20		25	ns
t _{LZWE} [10]	R/W HIGH to Low Z	3		3		3		3		ns
twDD[11]	Write Pulse to Data Delay		30		50		60		70	ns
t _{DDD} [11]	Write Data Valid to Read Data Valid		25		30		35		40	ns
BUSY TIMIN	$\mathbf{NG}^{[12]}$			•			•			
t _{BLA}	BUSY LOW from Address Match		15		20		20		45	ns
tBHA	BUSY HIGH from Address Mismatch	1	15		20		20		40	ns
tBLC	BUSY LOW from CE LOW		15		20		20		40	ns
t _{BHC}	BUSY HIGH from CE HIGH		15		20		20		35	ns
tps	Port Set-Up for Priority	5		5		5		5		ns
twB	R/W LOW after BUSY LOW	0		0	1	0		0		ns
t _{WH}	R/W HIGH after BUSY HIGH	13		20	T	30		40		ns
t _{BDD} [13]	BUSY HIGH to Data Valid		Note 13		Note 13		Note 13		Note 13	ns
	TIMING[12]									
t _{INS}	INT Set Time		15		25		25		30	ns
t _{INR}	INT Reset Time		15		25		25		30	ns
SEMAPHOR	RE TIMING						•			
t _{SOP}	SEM Flag Update Pulse (OE or SEM)	10		10		15	T	20	Π	ns
tswrd	SEM Flag Write to Read Time	- 5	†	5	İ	5		5		ns
tsps	SEM Flag Contention Window	5	_	5	†	5		5	<u> </u>	ns

Notes:

8. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OI}/I_{OH} and 30-pF load capacitance.

At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZOE} and t_{HZOE} is less than t_{LZOE}.
 Test conditions used are Load 3.

For information on part-to-part delay through RAM cells from writ-ing port to reading port, refer to Read Timing with Port-to-Port Delay waveform.

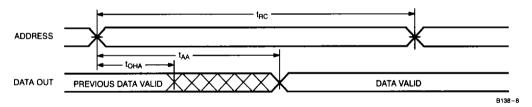
^{12.} Test conditions used are Load 2.

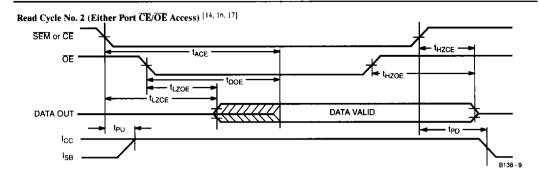
¹³ t_{BDD} is a calculated parameter and is the greater of t_{WDD} = t_{PWE} (actual) or t_{DDD} = t_{SD} (actual).



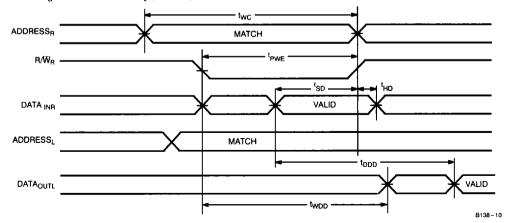
Switching Waveforms

Read Cycle No. 1 (Either Port Address Access)[14, 15]





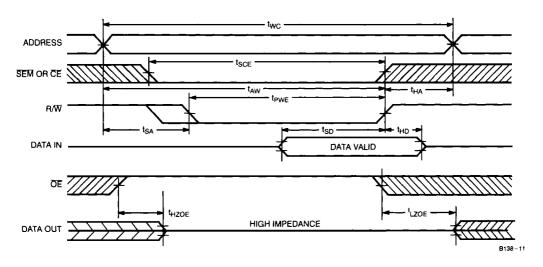
Read Timing with Port-to-Port Delay $(M/\overline{S} = L)^{[18, 19]}$



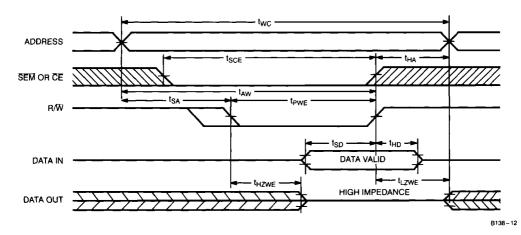
- Notes: 14. R/W is HIGH for read cycle.
- 15. Device is continuously selected $\overline{CE} = LOW$ and $\overline{OE} = LOW$. This waveform cannot be used for semaphore reads.
- Address valid prior to or coincident with CE transition LOW.
- 17. \(\overline{CE}_L = L\), \(\overline{SEM} = H\) when accessing RAM. \(\overline{CE} = H\), \(\overline{SEM} = L\) when accessing semaphores.
 18. \(\overline{BUSY} = HIGH\) for the writing port.
- 19. $\overline{CE}_L = \overline{CE}_R = LOW$.



Write Cycle No. 1: OE Three-States Data I/Os (Either Port)[20, 21, 22]



Write Cycle No. 2: R/W Three-States Data I/Os (Either Port)[20, 22, 23]

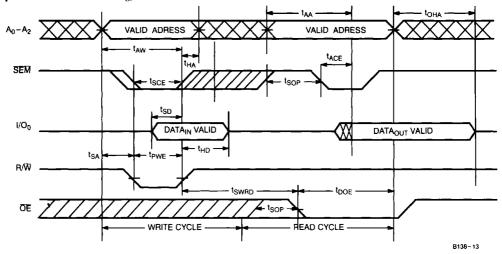


Notes:

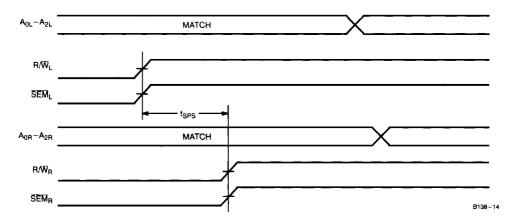
- Notes:
 The internal write time of the memory is defined by the overlap of CE or SEM LOW and R/W LOW. Both signals must be LOW to initiate a write, and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
 If OE is LOW during a R/W controlled write cycle, the write pulse width put by the least of the result o
- width must be the larger of tpwE or (tHZWE + tSD) to allow the I/O
- drivers to turn off and data to be placed on the bus for the required t_{SD} . If \overrightarrow{OE} is HIGH during a R/\overline{W} controlled write cycle (as in this example), this requirement does not apply and the write pulse can be as short as the specified tpwE
- 22. R/W must be HIGH during all address transitions.
- 23. Data I/O pins enter high impedance when \overline{OE} is held LOW during



Semaphore Read After Write Timing, Either Side^[24]



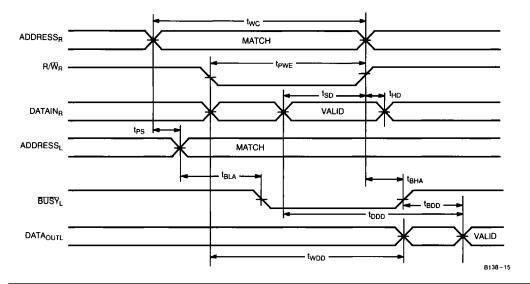
Timing Diagram of Semaphore Contention [25, 26, 27]



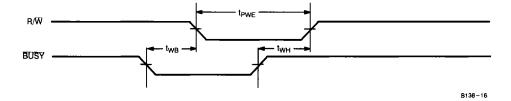
- Notes: 24. \overline{CE} = HIGH for the duration of the above timing (both write and read
- cycle). 25. $I/O_{0R} = I/O_{0L} = LOW$ (request semaphore); $\overline{CE}_R = \overline{CE}_L = HIGH$ 26. Semaphores are reset (available to both ports) at cycle start.
- If t_{SPS} is violated, the semaphore will definitely be obtained by one side or the other, but there is no guarantee which side will control the semaphore.



Timing Diagram of Read with \overline{BUSY} $(M/\overline{S} = HIGH)^{[19]}$



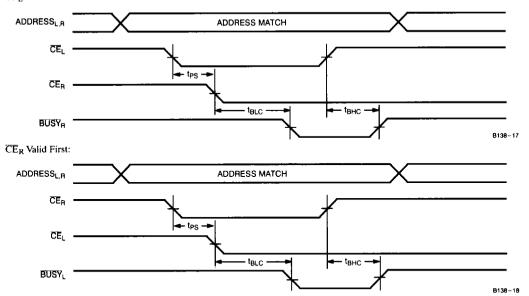
Write Timing with Busy Input $(M/\overline{S}=LOW)$





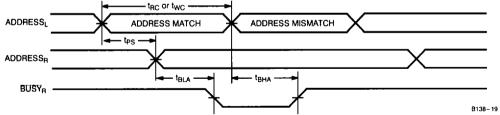
Busy Timing Diagram No. 1 $(\overline{\textbf{CE}}$ Arbitration)[28]

CEL Valid First:

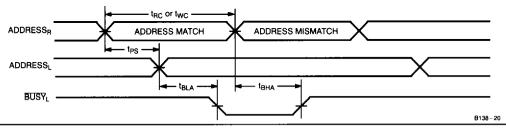


Busy Timing Diagram No. 2 (Address Arbitration)[28]

Left Address Valid First:



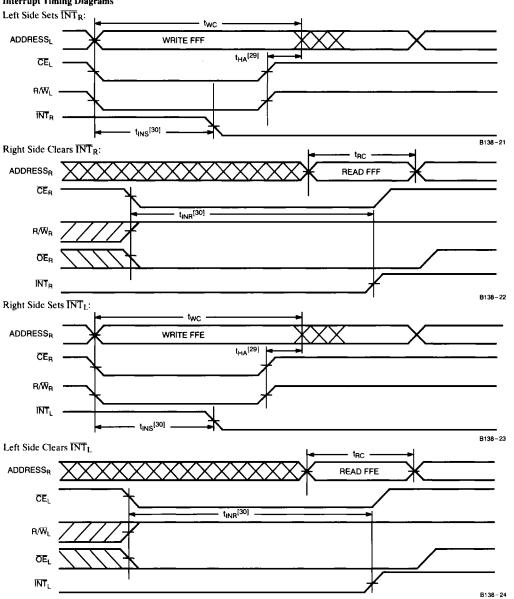
Right Address Valid First:



Note:
28. If tps is violated, the busy signal will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.



Interrupt Timing Diagrams



Notes: 29. t_{HA} depends on which enable pin (\overline{CE}_L or R/\overline{W}_L) is deasserted first. $30,\ t_{INS}$ or t_{INR} depends on which enable pin (\overline{CE}_L or $R/\overline{W}_L)$ is asserted last.



Architecture

The CY7B138/9 consists of an array of 4K words of 8/9 bits each of dual-port RAM cells, I/O and address lines, and control signals (CE, OE, R/W). These control pins permit independent access for reads or writes to any location in memory. To handle simultaneous writes/reads to the same location, a BUSY pin is provided on each port. Two interrupt (INT) pinscan be utilized for port-to-port communication. Two semaphore (SEM) control pins are used for allocating shared resources. With the M/S pin, the CY7B138/9 can function as a master (BUSY pins are outputs) or as a slave (BUSY pins are inputs). The CY7B138/9 has an automatic power-down feature controlled by CE. Each port is provided with its own output enable control (OE), which allows data to be read from the device.

Functional Description

Write Operation

Data must be set up for a duration of t_{SD} before the rising edge of R/W in order to guarantee a valid write. A write operation is controlled by either the ŌE pin (see Write Cycle No. 1 waveform) or the R/W pin (see Write Cycle No. 2 waveform). Data can be written to the device the Texas after the ŌE is deasserted or the the the falling edge of R/W. Required inputs for non-contention operations are summarized in Table 1.

If a location is being written to by one port and the opposite port attempts to read that location, a port-to-port flowthrough delay must be met before the data is read on the output; otherwise the data read is not deterministic. Data will be valid on the port t_{DDD} after the data is presented on the other port.

Read Operation

When reading the device, the user must assert both the OE and CE pins. Data will be available t_{ACE} after CE or t_{DOE} after OE is asserted. If the user of the CY7B138/9 wishes to access a semaphore flag, then the SEM pin must be asserted instead of the CE pin.

Interrupts

The interrupt flag (INT) permits communications between ports. When the left port writes to location FFF, the right port's interrupt flag (INT $_R$) is set. This flag is cleared when the right port reads that same location. Setting the left port's interrupt flag (INT $_L$) is accomplished when the right port writes to location FFE. This flag is cleared when the left port reads location FFE. The message at FFF or FFE is user-defined. See Table 2 for input requirements for INT. INT $_R$ and INT $_L$ are push-pull outputs and do not require pull-up resistors to operate. BUSY $_L$ and BUSY $_R$ in master mode are push-pull outputs and do not require pull-up resistors to operate.

Busy

The CY7B138/9 provides on-chip arbitration to alleviate simultaneous memory location access (contention). If both ports' $\overline{CE}s$ are asserted and an address match occurs within t_{PS} of each other the Busy logic will determine which port has access. If t_{PS} is violated, one port will definitely gain permission to the location, but it is not guaranteed which one. \overline{BUSY} will be asserted t_{BLA} after an address match or t_{BLC} after \overline{CE} is taken LOW.

Master/Slave

A M/S pin is provided in order to expand the word width by configuring the device as either a master or a slave. The BUSY output of the master is connected to the BUSY input of the slave. This will allow the device to interface to a master device with no external components. Writing of slave devices must be delayed until after the BUSY input has settled. Otherwise, the slave chip may begin a write cycle during a contention situation. When presented as a HIGH input, the M/S pin allows the device to be used as a master and therefore the BUSY line is an output. BUSY can then be used to send the arbitration outcome to a slave.

Semaphore Operation

The CY7B138/9 provides eight semaphore latches, which are separate from the dual-port memory locations. Semaphores are used to reserve resources that are shared between the two ports. The state of the semaphore indicates that a resource is in use. For example, if the left port wants to request a given resource, it sets a latch by writing a zero to a semaphore location. The left port then verifies its success in setting the latch by reading it. After writing to the semaphore. SEM or OE must be deasserted for tsop before attempting to read the semaphore. The semaphore value will be available t_{SWRD} + t_{DOE} after the rising edge of the semaphore write. If the left port was successful (reads a zero), it assumes control over the shared resource, otherwise (reads a one) it assumes the right port has control and continues to poll the semaphore. When the right side has relinquished control of the semaphore (by writing a one), the left side will succeed in gaining control of the a semaphore. If the left side no longer requires the semaphore, a one is written to cancel its request

Semaphores are accessed by asserting \overline{SEM} LOW. The \overline{SEM} pin functions as a chip enable for the semaphore latches (\overline{CE} must remain HIGH during \overline{SEM} LOW). A_{0-2} represents the semaphore address. \overline{OE} and R/W are used in the same manner as a normal memory access. When writing or reading a semaphore, the other address pins have no effect.

When writing to the semaphore, only I/O₀ is used. If a zero is written to the left port of an unused semaphore, a one will appear at the same semaphore address on the right port. That semaphore can now only be modified by the side showing zero (the left port in this case). If the left port now relinquishes control by writing a one to the semaphore, the semaphore will be set to one for both sides. However, if the right port had requested the semaphore (written a zero) while the left port had control, the right port would immediately own the semaphore as soon as the left port released it. *Table* 3 shows sample semaphore operations.

When reading a semaphore, all eight data lines output the semaphore value. The read value is latched in an output register to prevent the semaphore from changing state during a write from the other port. If both ports attempt to access the semaphore within tsps of each other, the semaphore will definitely be obtained by one side or the other, but there is no guarantee which side will control the semaphore.

Initialization of the semaphore is not automatic and must be reset during initialization program at power-up. All semaphores on both sides should have a one written into themn at initialization from both sides to assure that they will be free when needed.



Table 1. Non-Contending Read/Write

	Ing	outs		Outputs	
ĈĒ	R/W	ŌĒ	SEM	I/O ₀₋₇	Operation
Н	Х	Х	Н	High Z	Power-Down
Н	Н	L	L	Data Out	Read Data in Semaphore
Х	Х	Н	Х	High Z	I/O Lines Disabled
Н	7	Х	L	Data In	Write to Semaphore
L	Н	L	Н	Data Out	Read
L	L	Х	Н	Data In	Write
L	Х	Х	L		Illegal Condition

Table 2. Interrupt Operation Example (assumes $\overline{BUSY}_L = \overline{BUSY}_R = HIGH$)

	Left Port				Right Port					
Function	R/W	CE	ŌĒ	A ₀₋₁₁	INT	R/W	ĈĒ	ŌĒ	A_{0-11}	INT
Set Left INT	Х	X	X	X	L	L	L	Х	FFE	Х
Reset Left INT	Х	L	L	FFE	Н	Х	Х	Х	Х	Х
Set Right INT	L	L	Х	FFF	Х	X	Х	Х	Х	L
Reset Right INT	X	X	X	X	X	X	L	L	FFF	Н

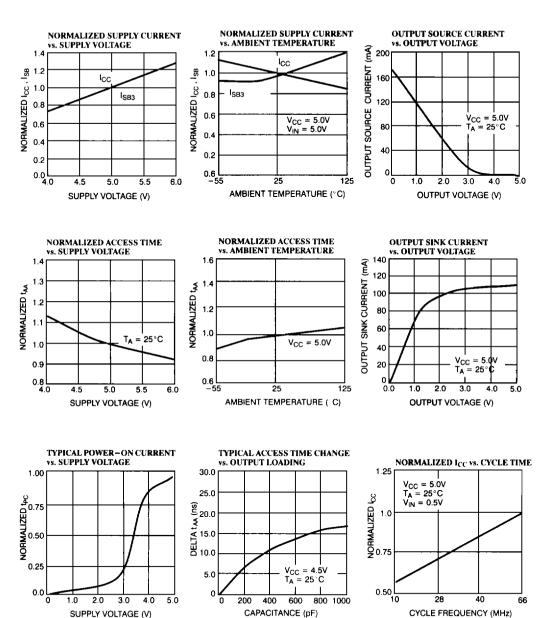
Table 3. Semaphore Operation Example

Function	I/O ₀ Left	I/O ₀ Right	Status
No action	1	1	Semaphore free
Left port writes semaphore	0	1	Left port obtains semaphore
Right port writes 0 to semaphore	0	1	Right side is denied access
Left port writes 1 to semaphore	1	0	Right port is granted access to semaphore
Left port writes 0 to semaphore	1	0	No change. Left port is denied access
Right port writes 1 to semaphore	0	1	Left port obtains semaphore
Left port writes 1 to semaphore	1	1	No port accessing semaphore address
Right port writes 0 to semaphore	1	0	Right port obtains semaphore
Right port writes 1 to semaphore	1	1	No port accessing semaphore
Left port writes 0 to semaphore	0	1	Left port obtains semaphore
Left port writes 1 to semaphore	1	1	No port accessing semaphore



Typical DC and AC Characteristics

SUPPLY VOLTAGE (V)





Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7B138-15JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
25	CY7B138-25JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
	CY7B138-25JI	J81	68-Lead Plastic Leaded Chip Carrier	Industrial
	CY7B138-25LMB	L81	68-Square Leadless Chip Carrier	Military
35	CY7B138-35JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
	CY7B138-35JI	J81	68-Lead Plastic Leaded Chip Carrier	Industrial
	CY7B138-35LMB	L81	68-Square Leadless Chip Carrier	Military
55	CY7B138-55JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
	CY7B138-55JI	J81	68-Lead Plastic Leaded Chip Carrier	Industrial

Speed (ns)	Ordering Code	Package Type	Package Type	Operating Range
15	CY7B139-15JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
25	CY7B139-25JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
	CY7B139-25JI	J81	68-Lead Plastic Leaded Chip Carrier	Industrial
	CY7B139-25LMB	L81	68-Square Leadless Chip Carrier	Military
35	CY7B139-35JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
	CY7B139-35JI	J81	68-Lead Plastic Leaded Chip Carrier	Industrial
	CY7B139-35LMB	L81	68-Square Leadless Chip Carrier	Military
55	CY7B139-55JC	J81	68-Lead Plastic Leaded Chip Carrier	Commercial
	CY7B139-55JI	J81	68-Lead Plastic Leaded Chip Carrier	Industrial



MILITARY SPECIFICATIONS Group A Subgroup Testing DC Characteristics

Parameter	Subgroups
V _{OH}	1, 2, 3
V _{OL}	1, 2, 3
V _{IH}	1, 2, 3
V _{IL} Max.	1, 2, 3
I _{IX}	1, 2, 3
I _{OZ}	1, 2, 3
1 _{CC}	1, 2, 3
I _{SB1}	1, 2, 3
I _{SB2}	1, 2, 3
I _{SB3}	1, 2, 3
I _{SB4}	1, 2, 3

Switching Characteristics

Parameter Parameter	Subgroups			
READ CYCLE				
t _{RC}	7, 8, 9, 10, 11			
t _{AA}	7, 8, 9, 10, 11			
toha	7, 8, 9, 10, 11			
t _{ACE}	7, 8, 9, 10, 11			
t _{DOE}	7, 8, 9, 10, 11			
WRITE CYCLE				
twc	7, 8, 9, 10, 11			
t _{SCE}	7, 8, 9, 10, 11			
t _{AW}	7, 8, 9, 10, 11			
t _{HA}	7, 8, 9, 10, 11			
t _{SA}	7, 8, 9, 10, 11			
t _{PWE}	7, 8, 9, 10, 11			
t _{SD}	7, 8, 9, 10, 11			
t _{HD}	7, 8, 9, 10, 11			
BUSY/INTERRUPT TIMING				
t _{BLA}	7, 8, 9, 10, 11			
t _{BHA}	7, 8, 9, 10, 11			
tBLC	7, 8, 9, 10, 11			
t _{BHC}	7, 8, 9, 10, 11			
t _{PS}	7, 8, 9, 10, 11			
t _{INS}	7, 8, 9, 10, 11			
t _{INR}	7, 8, 9, 10, 11			
BUSY TIMING				
t _{WB}	7, 8, 9, 10, 11			
t _{WH}	7, 8, 9, 10, 11			
t _{BDD}	7, 8, 9, 10, 11			
t _{DDD}	7, 8, 9, 10, 11			
t _{WDD}	7, 8, 9, 10, 11			

Document #: 38-00162-G